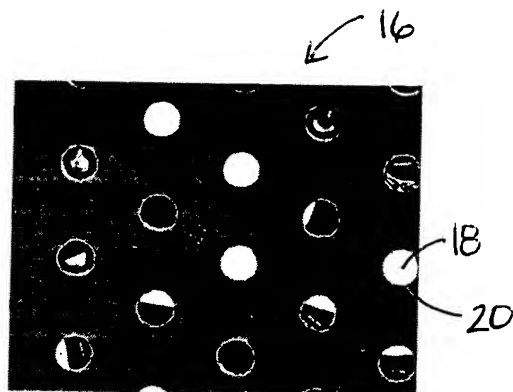


(a) Integrity of Pt/SBT/Ir-Ta-O capacitor with Al_2O_3 layer (325 Å, oxidation annealed at 500°C for 30min, forming gas annealed at 400°C for 5min)

FIG. 1
(PRIOR ART)



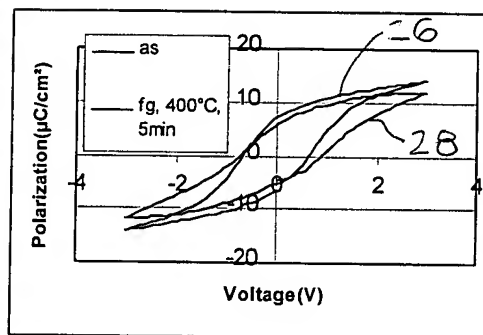
(b) Integrity of Pt/SBT/Ir-Ta-O capacitor with TiO_2 passivation layer (800Å, oxygen annealing at 500°C for 30 min.

FIG. 2
(PRIOR ART)



(c) Integrity of Pt/SBT/Ir-Ta-O capacitor with Al-Ti-O 226 Å, O_2 annealed at 500°C for 30min, Forming gas annealed at 400°C for 5min

FIG. 3



(d) heteresis loop of Pt/SBT/Ir-Ta-O capacitor with Al-Ti-O (oxidation annealed at 500°C) before and after forming gas annealing at 400°C for 5min

FIG. 4

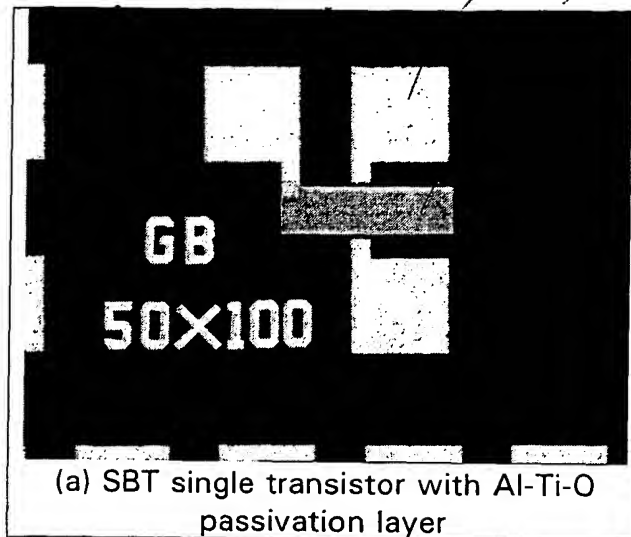


FIG. 5

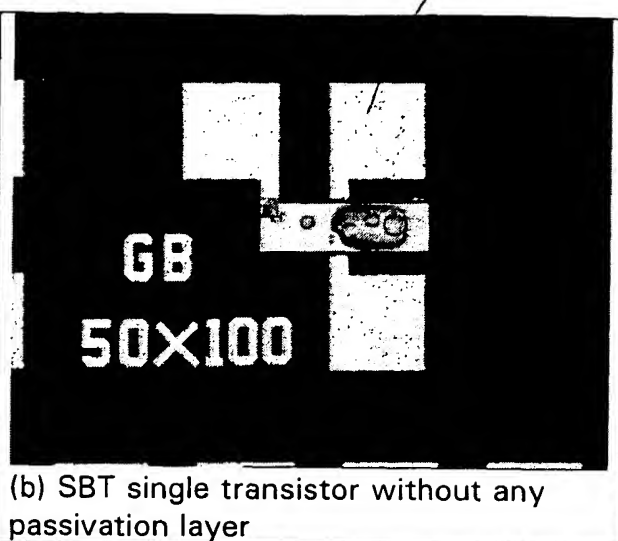


FIG. 7

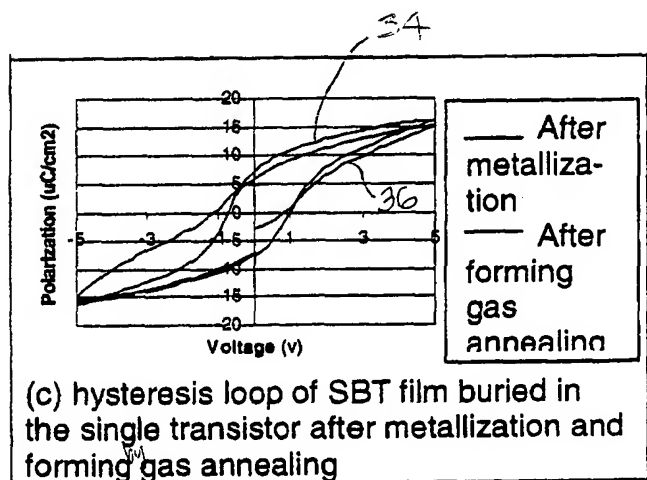


FIG. 6

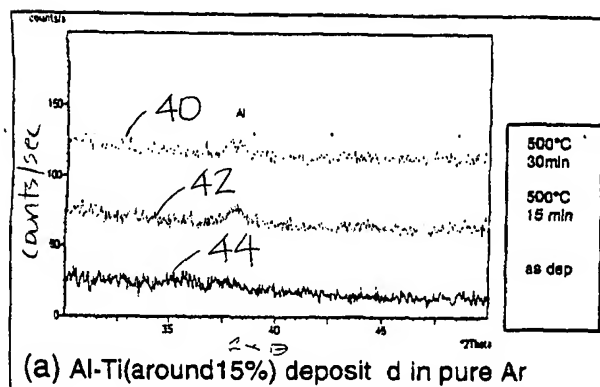


FIG. 8

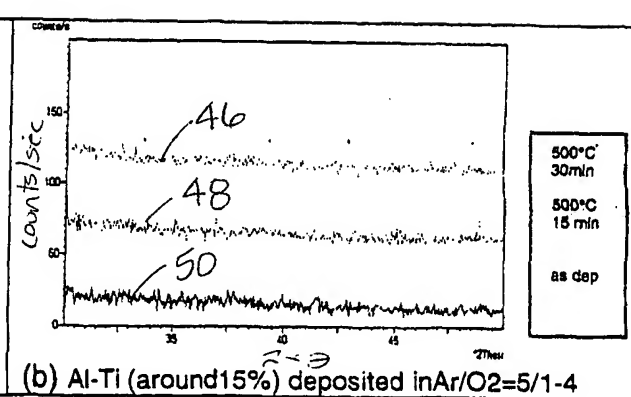


FIG. 9

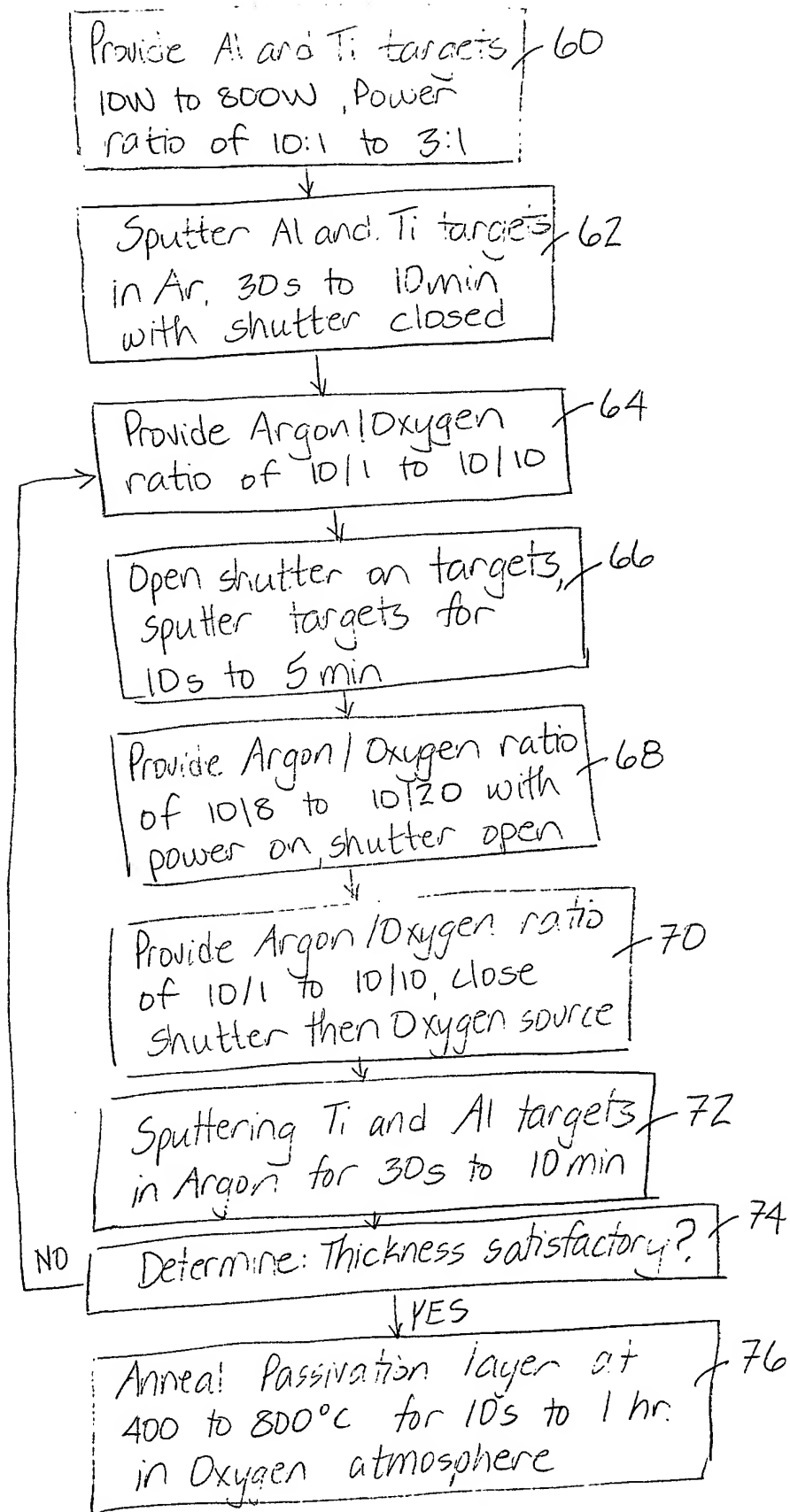


FIG. 10